

## ABSTRACT OF THE DISCLOSURE

The present invention discloses method for manufacturing semiconductor device employing an EXTIGATE  
5 structure. In accordance with the method, a predetermined thickness of the device isolation film is etched to form a recess. The recess is then filled with a second nitride film. A stacked structure of a barrier metal film, a metal layer and a third nitride film on the second nitride film and the  
10 polysilicon film is formed on the entire surface and the etched via a photoetching process to form a gate electrode. An insulating film spacer is deposited on a sidewall of the gate electrode. The exposed portion of the polysilicon film using the third nitride film pattern and the insulating film  
15 spacer as a mask to form a polysilicon film pattern and an oxide film on a sidewall of the polysilicon film pattern.